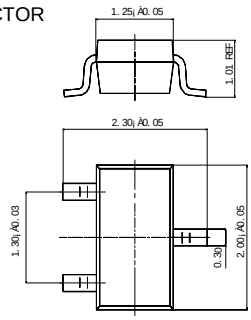
2SB1218A TRANSISTOR (PNP)

SOT-323

1. BASE
2. EMITTER
3. COLLECTOR



Unit: mm

FEATURES

Power dissipation

P_{CM}: 150 mW (Tamb=25℃)

Collector current

I_{CM}: -100 mA

Collector-base voltage

$V_{(BR)CBO}$: -45 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic=-10μA, I_E=0	-45			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic=-2mA, I_B=0	-45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-10μA, I_C=0	-7			V
Collector cut-off current	I_{CBO}	V_{CB}=-20V, I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-6V, I_C=0			-0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-10V, I_C=-2mA	160		460	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-100mA, I_B=-10mA			-0.5	V
Transition frequency	f_T	V_{CE}=-10V, I_C=-1mA , f=200MHz		80		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz		2.7		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	**Q**	**R**	**S**
Range	160-260	210-340	290-460
Marking	**BQ**	**BR**	**BS**